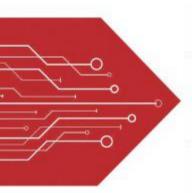
# MSKSEMI SEMICONDUCTOR















**ESD** 

TVS

TSS

MOV

**GDT** 

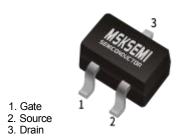
**PLED** 

Product data sheet







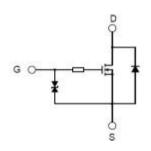


SOT-523

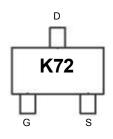
### **Specification Features:**

- Low On-resistance
- Low Gate Threshold Voltage
- Low Input capacitance
- ESD Protected up to 1kV (HBM)
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

### **Electrical Symbol:**







**Absolute Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-Source Voltage	60	V
V <sub>GS</sub>	Continuous Gate-Source Voltage	<b>±</b> 20V	V
ID	Continuous Drain Current	115	mA
P <sub>D</sub>	Power Dissipation	150	mW
Reja	Thermal Resistance from Junction to Ambient	833	°C /W
T <sub>STG</sub>	Storage Temperature Range	-55 to +150	°C
TJ	Operating Junction Temperature	+150	°C









Cymhol	Parameter	Test Condition	Limits			Linit
Symbol	Parameter	rest Condition	Min	Тур	Max	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =10uA	60			Volts
I <sub>GSS</sub>	Gate-Body Leakage	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±1	uA
loss	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			100	nA

#### On Characteristics

Cymphol	Parameter	Test Condition	Limits			l lmi4
Symbol		rest Condition	Min	Тур	Max	Unit
Vth(GS)	Gate-Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250uA	1		2.5	Volts
ID(ON)	On-state Drain Current	V <sub>GS</sub> =10V, V <sub>DS</sub> =7V	500			mA
RDS(on)	Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA			7.5	Ω
		V <sub>GS</sub> =5V, I <sub>D</sub> =50mA			7.5	Ω
<b>g</b> fs	Forward Trans Conductance	V <sub>DS</sub> =10V, I <sub>D</sub> =200mA	80		500	ms
<b>V</b> DS(on)	Drain-Source On-Voltage	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA			3.75	V
		V <sub>GS</sub> =5V, I <sub>D</sub> =50mA			0.375	V
<b>V</b> sd	Diode Forward Voltage	I <sub>S</sub> =250mA, V <sub>G</sub> S=0V			1	V

**Dynamic Characteristics** 

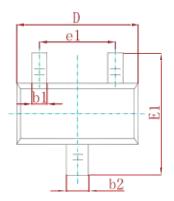
Cymphol	Downwoodow	Took Condition	Limits			1114
Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
Ciss	Input Capacitance				50	pF
Coss	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz			25	pF
Crss	Reverse Transfer Capacitance				5.0	pF

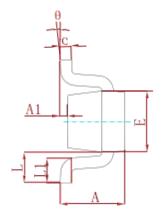
**Switching Characteristics** 

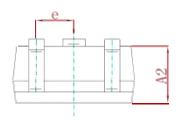
Cymbol	Parameter	Test Condition	Limits			Unit
Symbol	rai ai illetei	rest Condition	Min	Тур	Max	Unit
t <sub>D(on)</sub>	Turn-on Time	$V_{DD}$ =10V, $R_L$ =20 $\Omega$ ,		5.6		nS
t <sub>D(off)</sub>	Turn-off Time	$I_D$ =500mA, $V_{GEN}$ =10V, $R_G$ = 10 $\Omega$		25		nS



# **PACKAGE MECHANICAL DATA**

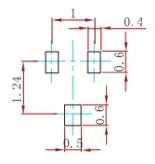






	Dimensions	In Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
С	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
е	0.500	0.500 TYP.		TYP.
e1	0.900	1.100	0.035	0.043
L	0.400	REF.	0.016	REF.
L1	0.260	0.460	0.010	0.018
A	O°.	۵°	O°	8°

# Suggested Pad Layout



- 1.Controlling dimension in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY			
2N7002T-MS	SOT-523	3000			



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TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7

NTE2384 NTE2969 NTE6400A DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7

BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IRF40SC240ARMA1 IPS60R1K0PFD7SAKMA1

IPS60R360PFD7SAKMA1 IPS60R600PFD7SAKMA1